

# PBHV9040X

500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor

9 December 2013

Product data sheet

## 1. General description

PNP high-voltage low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8540X.

## 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain ( $h_{FE}$ ) at high  $I_C$
- AEC-Q101 qualified

## 3. Applications

- Electronic ballast for fluorescent lighting
- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch mode power supply

## 4. Quick reference data

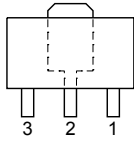
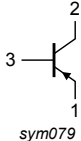
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0\text{ V}$	-	-	-500	V
$V_{CEO}$	collector-emitter voltage	open base	-	-	-400	V
$I_C$	collector current		-	-	-0.25	A
$h_{FE}$	DC current gain	$V_{CE} = -10\text{ V}; I_C = -50\text{ mA}; T_{amb} = 25\text{ }^\circ\text{C}$	100	200	-	



## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 <p style="text-align: center;"><b>SOT89</b></p>	 <p style="text-align: center;"><i>sym079</i></p>
2	C	collector		
3	B	base		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBHV9040X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV9040X	%4E

[1] % = placeholder for manufacturing site code

## 8. Limiting values

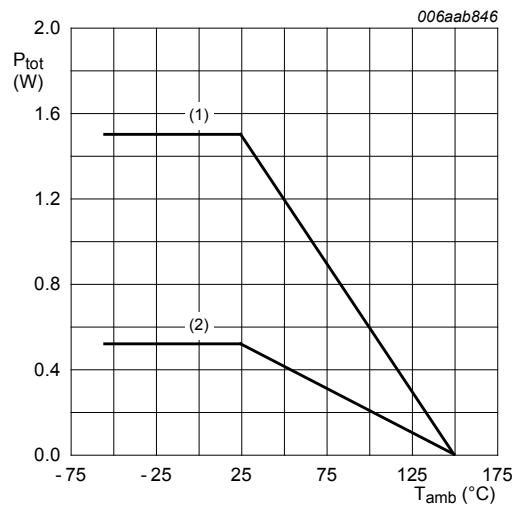
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-500	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-400	V
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	-500	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-0.25	A
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-0.5	A
I <sub>BM</sub>	peak base current			-	-200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.52	W
			[2]	-	1.5	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



(1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>

(2) FR4 PCB, standard footprint

**Fig. 1. Power derating curves**

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	240	K/W
			[2]	-	-	83	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

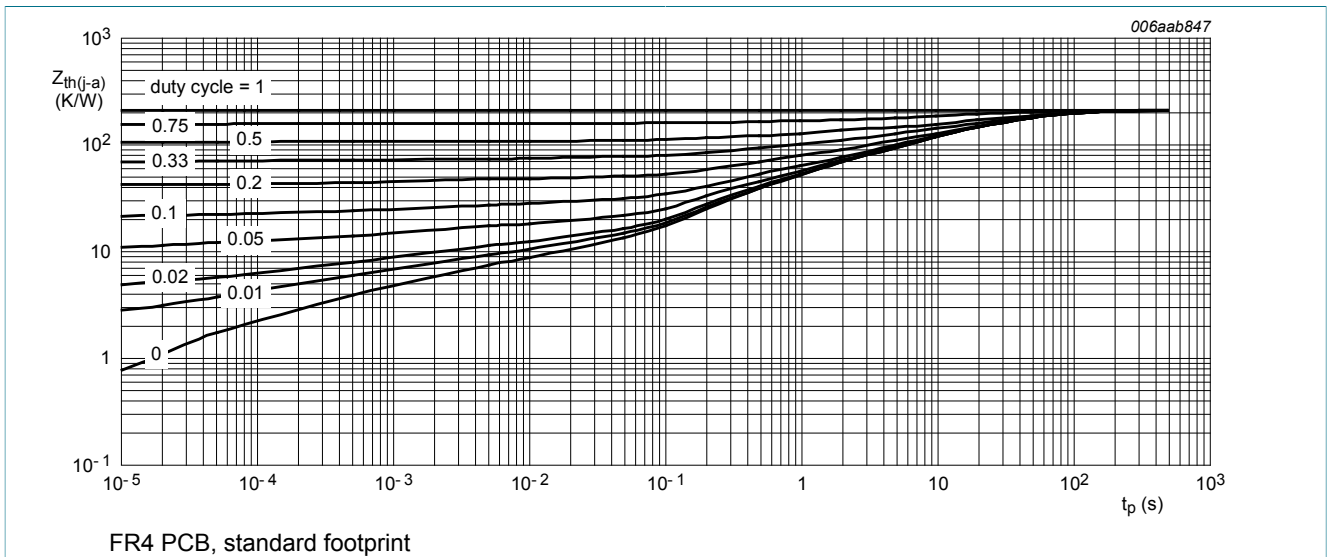


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

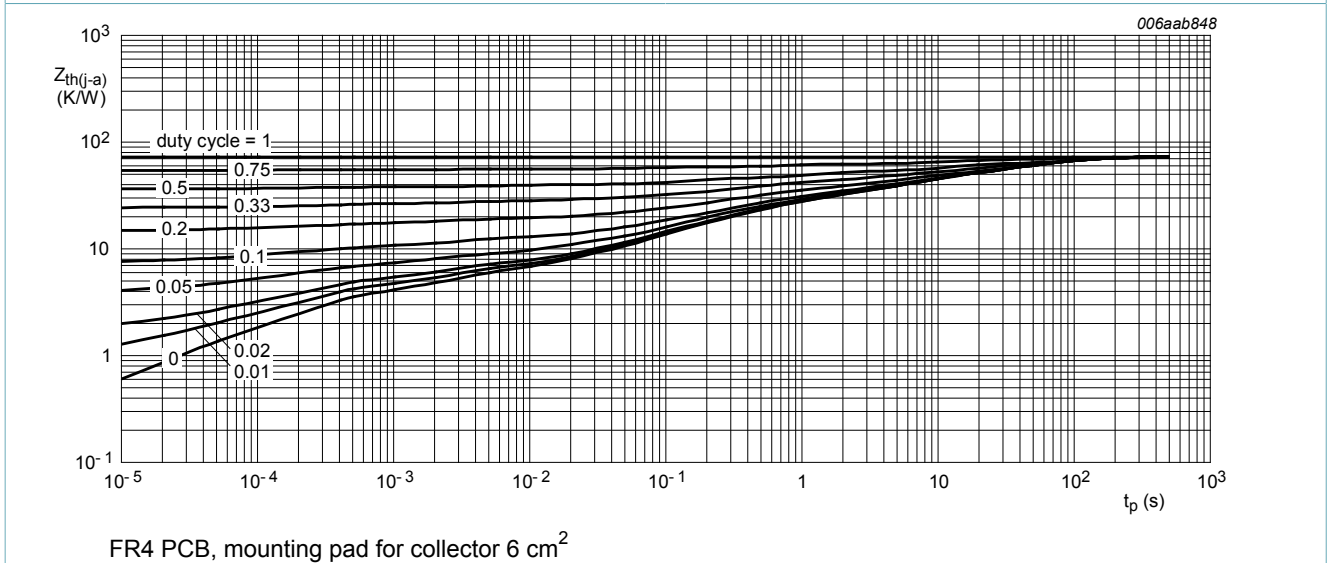


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = -320 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
		V <sub>CB</sub> = -320 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-10	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -320 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -50 mA; T <sub>amb</sub> = 25 °C	100	200	-	
		V <sub>CE</sub> = -10 V; I <sub>C</sub> = -100 mA; T <sub>amb</sub> = 25 °C	80	200	-	
		V <sub>CE</sub> = -10 V; I <sub>C</sub> = -250 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	10	25	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -100 mA; I <sub>B</sub> = -20 mA; T <sub>amb</sub> = 25 °C	-	-110	-200	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -100 mA; I <sub>B</sub> = -20 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-1	-1.1	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -2 V; I <sub>C</sub> = -0.15 A; I <sub>Bon</sub> = -0.03 A; I <sub>Boff</sub> = 0.03 A; T <sub>amb</sub> = 25 °C	-	9	-	ns
t <sub>r</sub>	rise time		-	1810	-	ns
t <sub>on</sub>	turn-on time		-	1819	-	ns
t <sub>s</sub>	storage time		-	715	-	ns
t <sub>f</sub>	fall time		-	1085	-	ns
t <sub>off</sub>	turn-off time		-	1800	-	ns
f <sub>T</sub>	transition frequency		V <sub>CE</sub> = -10 V; I <sub>C</sub> = -10 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	55	-
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -20 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	7	-	pF
C <sub>e</sub>	emitter capacitance	V <sub>EB</sub> = -0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	150	-	pF

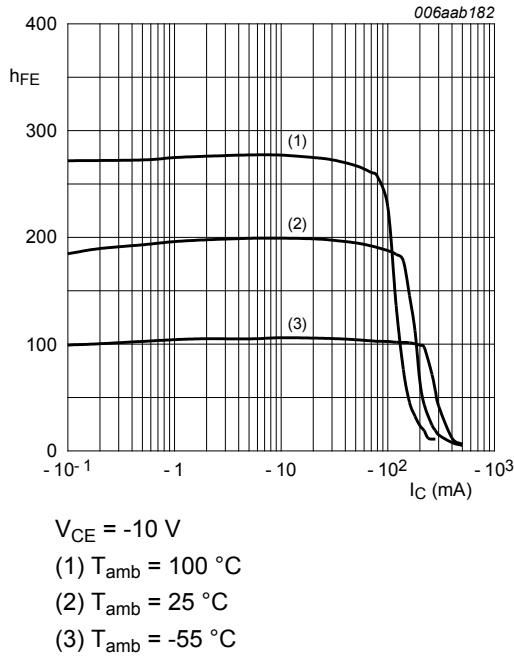


Fig. 4. DC current gain as a function of collector current; typical values

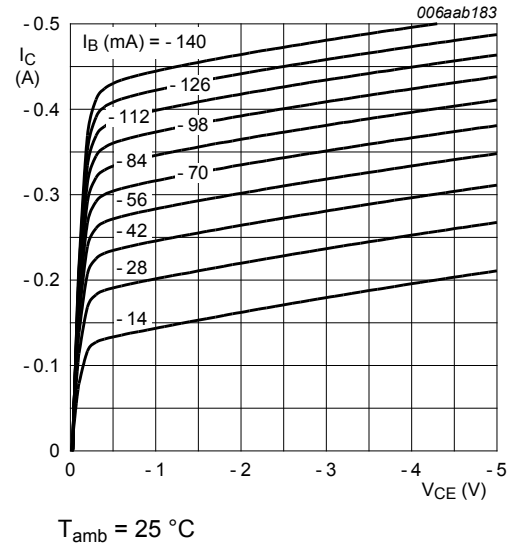


Fig. 5. Collector current as a function of collector-emitter voltage; typical values

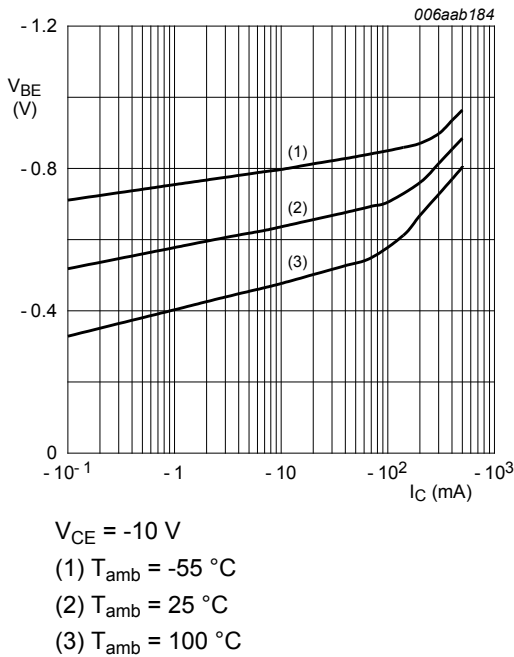


Fig. 6. Base-emitter voltage as a function of collector current; typical values

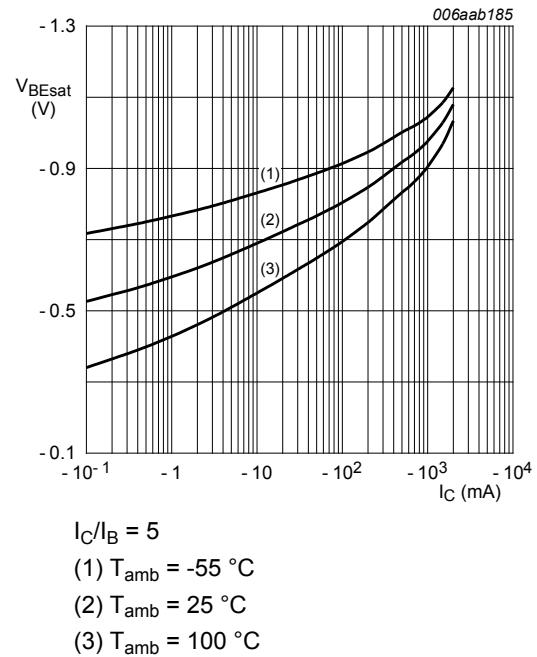
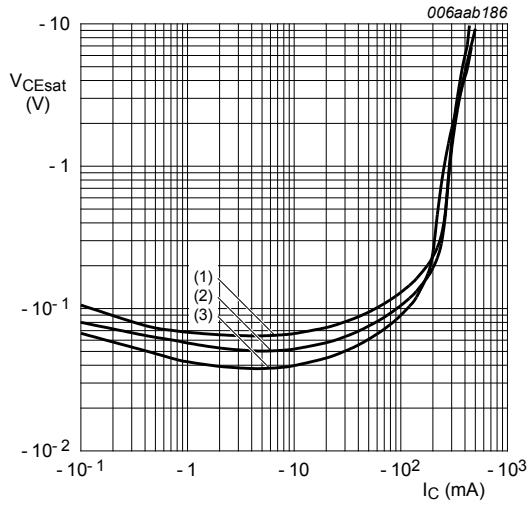


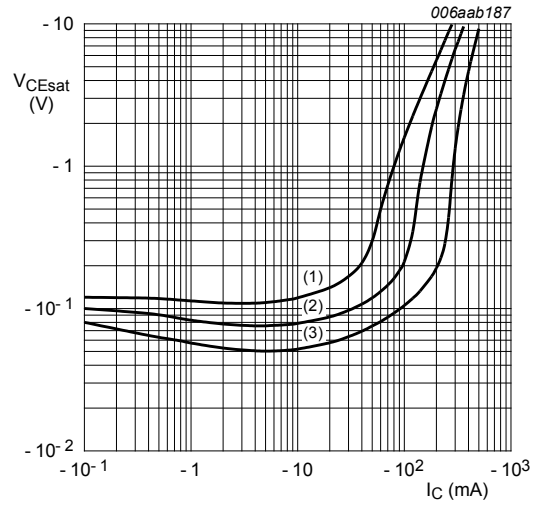
Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

500 V, 0.25 A PNP high-voltage low VCEsat (BISS) transistor



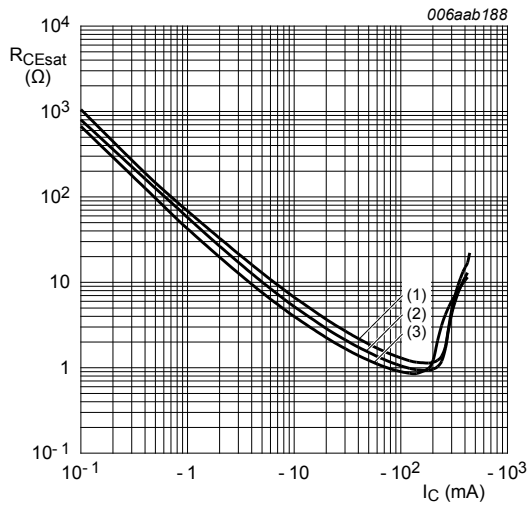
$I_C/I_B = 5$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values**



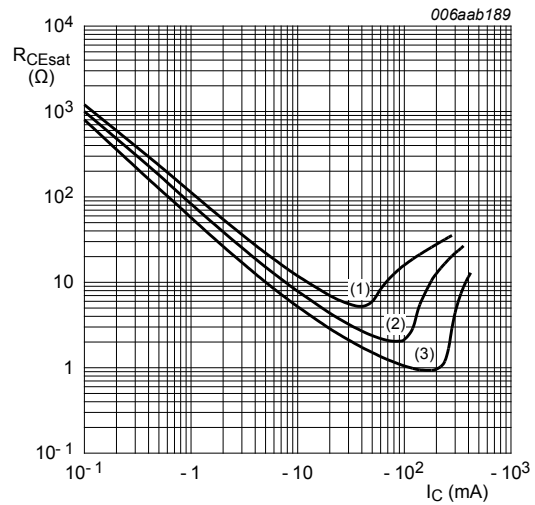
$T_{amb} = 25\text{ }^\circ\text{C}$   
 (1)  $I_C/I_B = 20$   
 (2)  $I_C/I_B = 10$   
 (3)  $I_C/I_B = 5$

**Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values**



$I_C/I_B = 5$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values**



$T_{amb} = 25\text{ }^\circ\text{C}$   
 (1)  $I_C/I_B = 20$   
 (2)  $I_C/I_B = 10$   
 (3)  $I_C/I_B = 5$

**Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values**

### 11. Test information

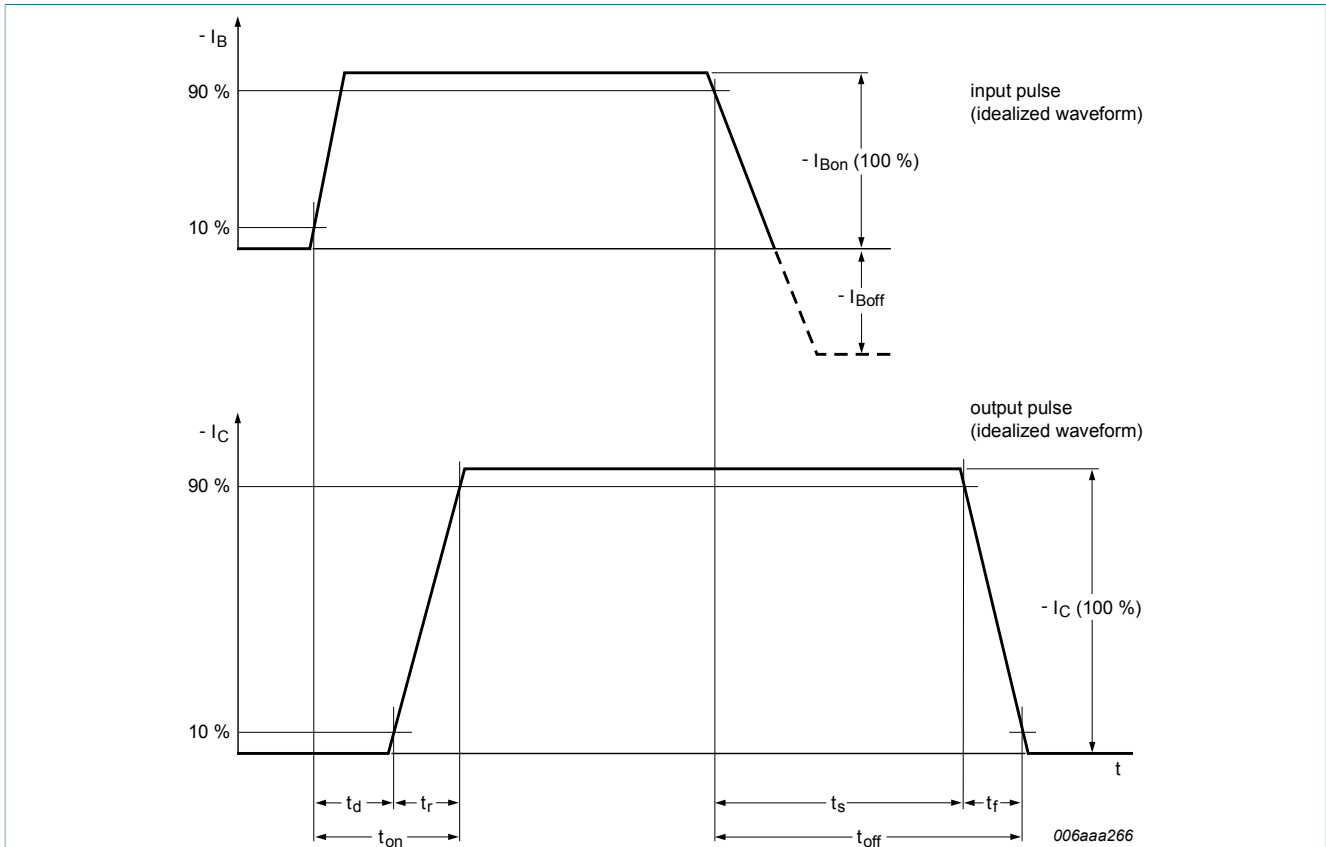


Fig. 12. BISS transistor switching time definition

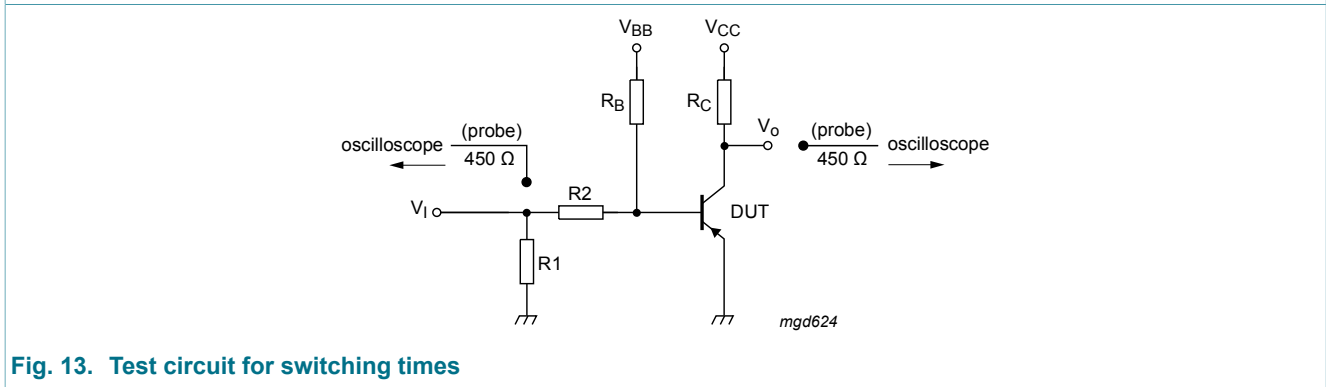


Fig. 13. Test circuit for switching times

#### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.



## 12. Package outline

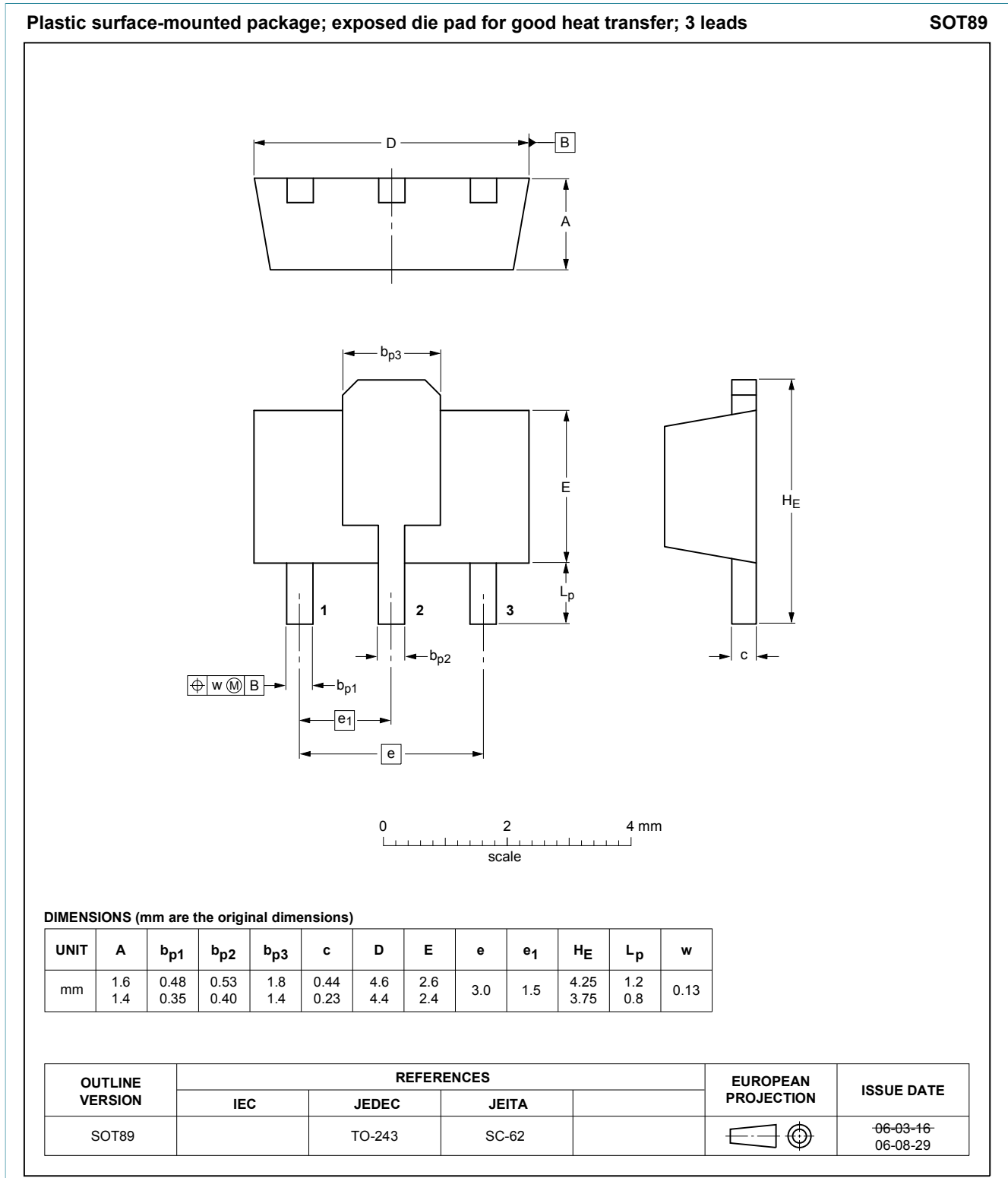
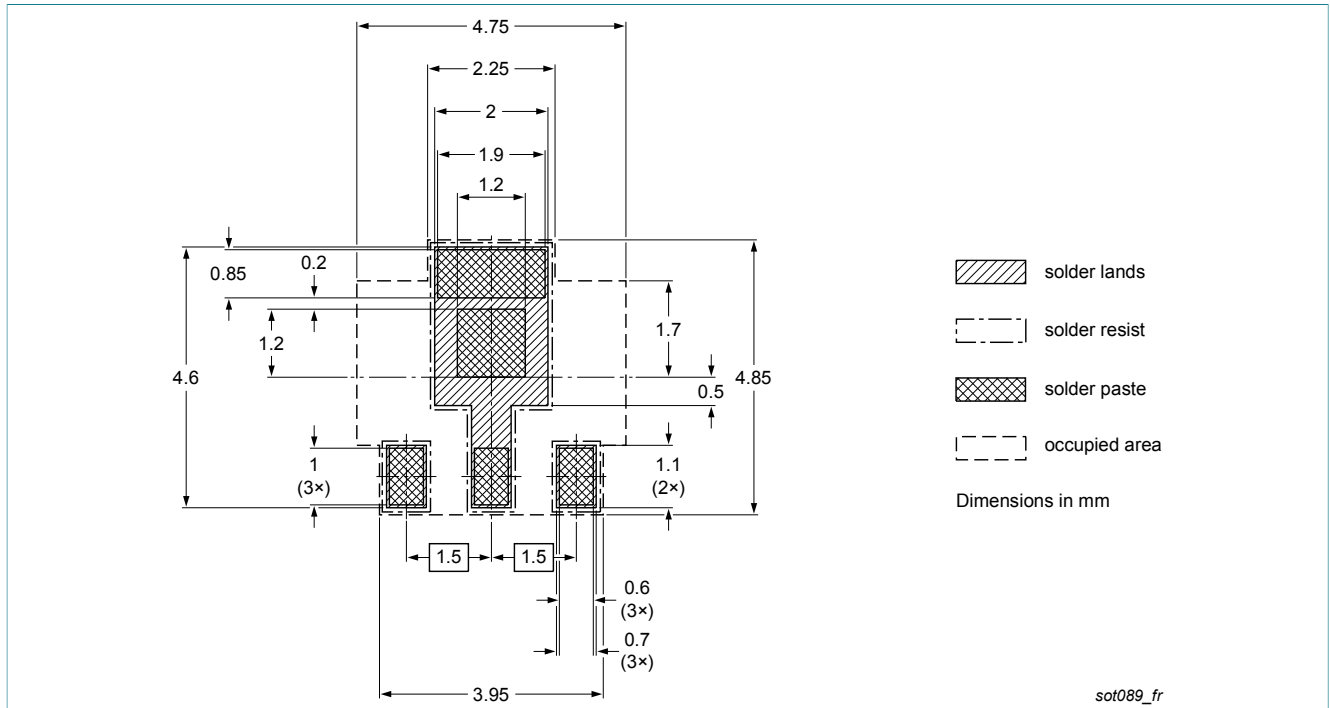
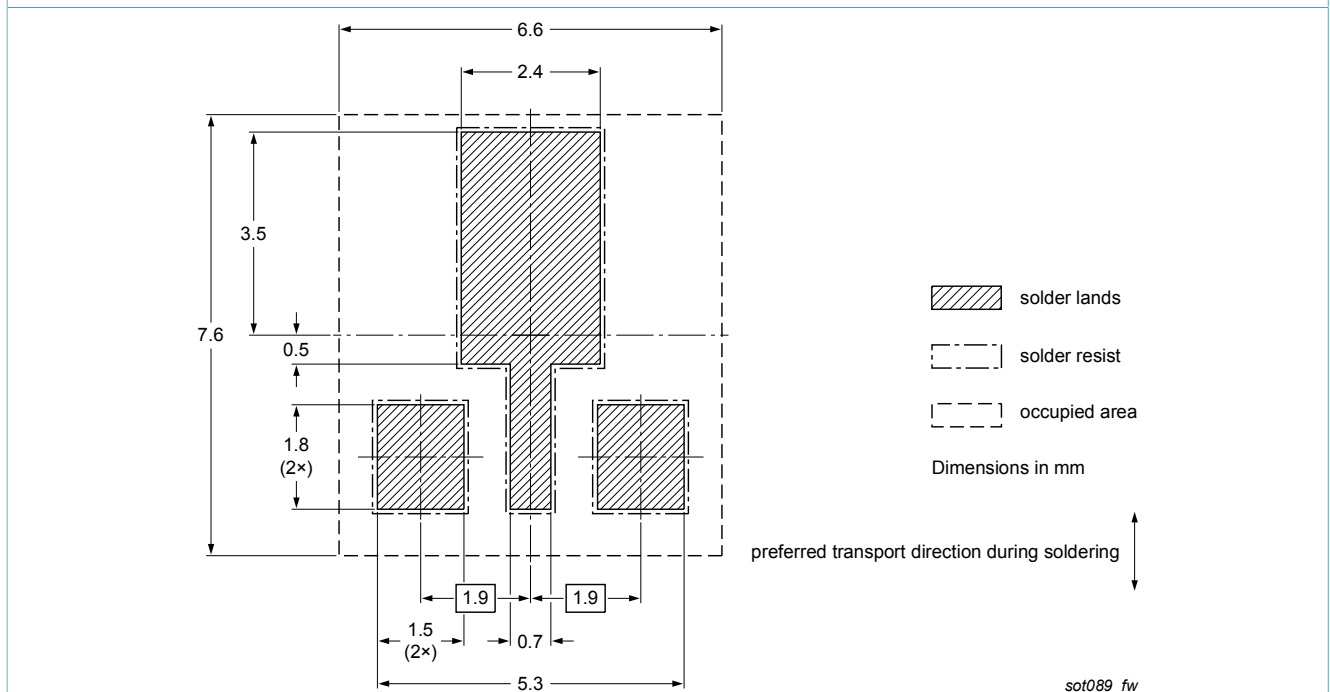


Fig. 14. Package outline SOT89

### 13. Soldering



**Fig. 15. Reflow soldering footprint for SOT89**



**Fig. 16. Wave soldering footprint for SOT89**

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9040X v.1	20131209	Product data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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